Bastard

List of Publications by Year
in descending order

23 papers	4,503 citations	394421 19 h-index	642732 23 g-index
23 all docs	23 docs citations	23 times ranked	2106 citing authors

#	Article	IF	Citations
1	Exciton capture by shallow quantum wells in separate confinement heterostructures. Physical Review B, 1996, 54, 5629-5636.	3.2	9
2	Photoluminescence of Single InAs Quantum Dots Obtained by Self-Organized Growth on GaAs. Physical Review Letters, 1994, 73, 716-719.	7.8	1,053
3	Spin-flip relaxation time of quantum-well electrons in a strong magnetic field. Physical Review B, 1992, 46, 4253-4256.	3.2	25
4	Interband absorption in quantum wires. II. Nonzero-magnetic-field case. Physical Review B, 1992, 45, 1700-1704.	3.2	57
5	Hole polarization and slow hole-spin relaxation in ann-doped quantum-well structure. Physical Review B, 1992, 46, 7292-7295.	3.2	50
6	Interband absorption in quantum wires. I. Zero-magnetic-field case. Physical Review B, 1992, 45, 1688-1699.	3.2	180
7	â€˜â€˜Spinâ€™â€™-flip scattering of holes in semiconductor quantum wells. Physical Review B, 1991, 43, 9687-9691.	3.2	158
8	Phonon scattering and energy relaxation in two-, one-, and zero-dimensional electron gases. Physical Review B, 1990, 42, 8947-8951.	3.2	942
9	Subpicosecond luminescence study of tunneling and relaxation in coupled quantum wells. Physical Review B, 1990, 42, 7021-7032.	3.2	81
10	Spin-flip relaxation time of conduction electrons inCd1â^’xMnxTe quantum wells. Physical Review B, 1990, 41, 7899-7902.	3.2	57
11	Dimensionality effects on the interband magnetoelectroabsorption of semiconductor superlattices. Physical Review B, 1990, 42, 11404-11407.	3.2	22
12	Density dependence of radiative and nonradiative recombination rates in a gatedGaAs/Ga1â^’xAlxAsmodulation-doped quantum well. Physical Review B, 1989, 39, 13537-13540.	3.2	13
13	Evaluation of some scattering times for electrons in unbiased and biased single- and multiple-quantum-well structures. Physical Review B, 1989, 40, 1074-1086.	3.2	382
14	Miniband dispersion and excitonic effects on the optical spectra of GaAs/AlxGa1â^’xAs superlattices. Physical Review B, 1989, 40, 5802-5805.	3.2	40
15	Electric-Field-Induced Localization and Oscillatory Electro-optical Properties of Semiconductor Superlattices. Physical Review Letters, 1988, 60, 220-223.	7.8	441
16	Wannier-Stark levels in the valence band of semiconductor multiple quantum wells. Physical Review B, 1988, 38, 8406-8411.	3.2	21
17	Many-Body Effects in a Modulation-Doped Semiconductor Quantum Well. Physical Review Letters, 1987, 59, 2690-2692.	7.8	162
18	Observation of Carrier Localization in Intentionally Disordered Gaas/Gaalas Superlattices. Physical Review Letters, 1986, 57, 1464-1467.	7.8	183

#	Article	IF	Citations
19	Resonant carrier capture by semiconductor quantum wells. Physical Review B, 1986, 33, 1420-1423.	3.2	226
20	Spectroscopy of a high-mobility GaAs-Ga1â^'xAlxAs one-side-modulation-doped quantum well. Physical Review B, 1986, 34, 2482-2485.	3.2	69
21	Transient photovoltaic effect in semiconductor superlattices. Physical Review B, 1986, 33, 1063-1066.	3.2	30
22	Electric-field-induced dissociation of excitons in semiconductor quantum wells. Physical Review B, 1985, 31, 3893-3898.	3.2	197
23	Size quantization and band-offset determination in GaAs-GaAlAs separate confinement heterostructures. Physical Review B, 1985, 31, 5539-5542.	3.2	105